PATENT APPLICATION DOCKET NO.: 1263-0025US VIRP72

ABSTRACT OF THE DISCLOSURE

A source-biasing mechanism for leakage reduction in SRAM. In standby mode, wordlines are deselected and a source-biasing potential is provided to SRAM cells. In read mode, a selected wordline deactivates the source-biasing potential provided to the selected row of SRAM cells, whereas the remaining SRAM cells on the selected bitline column continue to be source-biased.